WR0553I ṂṂÞ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-220F Plastic Package.

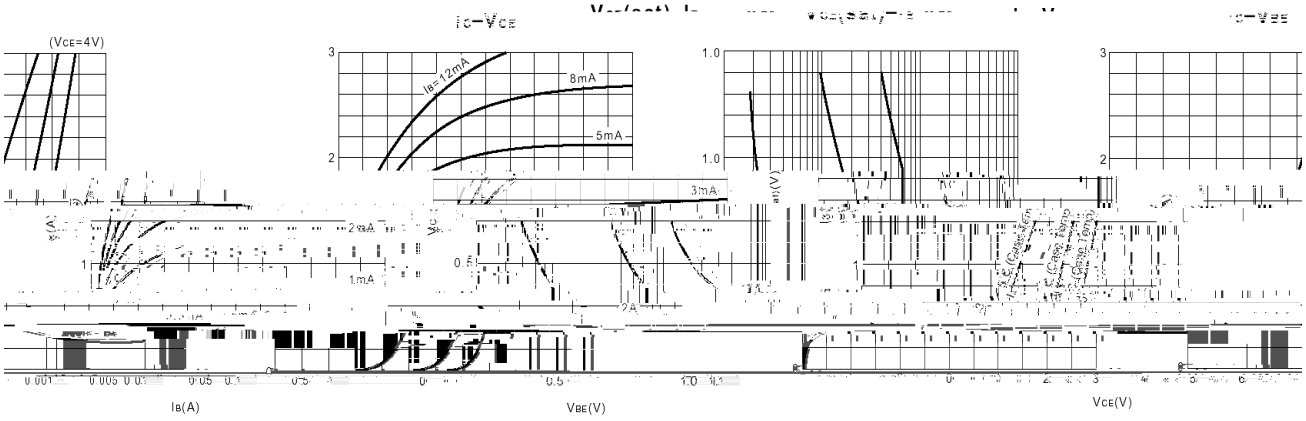
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High $h_{FE}$, low V

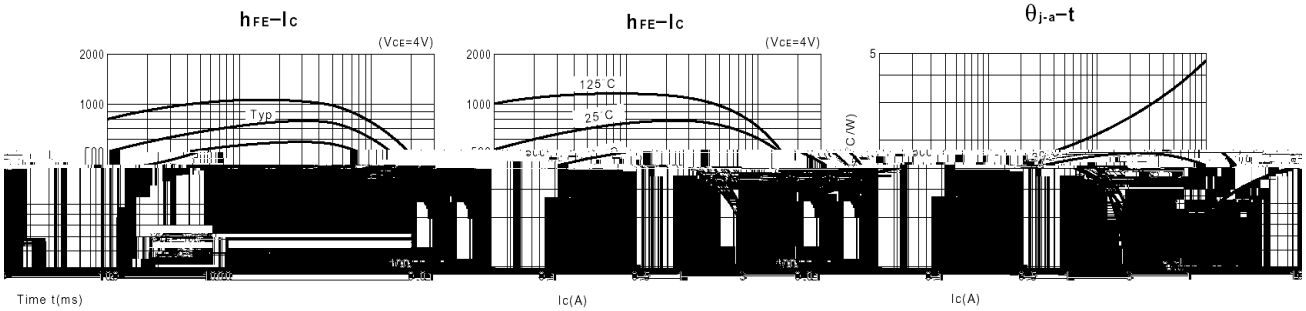
| v ̈Ω<br>Parameter | ϒ N<br>Symbol | ̈Ω Ö<br>Rating | D Ч<br>Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | 80 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 60 | V |
| Emitter to Base Voltage | $V_{EBO}$ | 6.0 | V |
| Collector Current - Continuous | $I_C$ | 3.0 | A |
| Base Current | $I_B$ | 1.0 | A |
| Collector Power Dissipation | $P_C$(Tc=25 ) | 25 | W |
| Junction Temperature | $T_j$ | 150 | |
| Storage Temperature Range | $T_{stg}$ | -55 150 | |

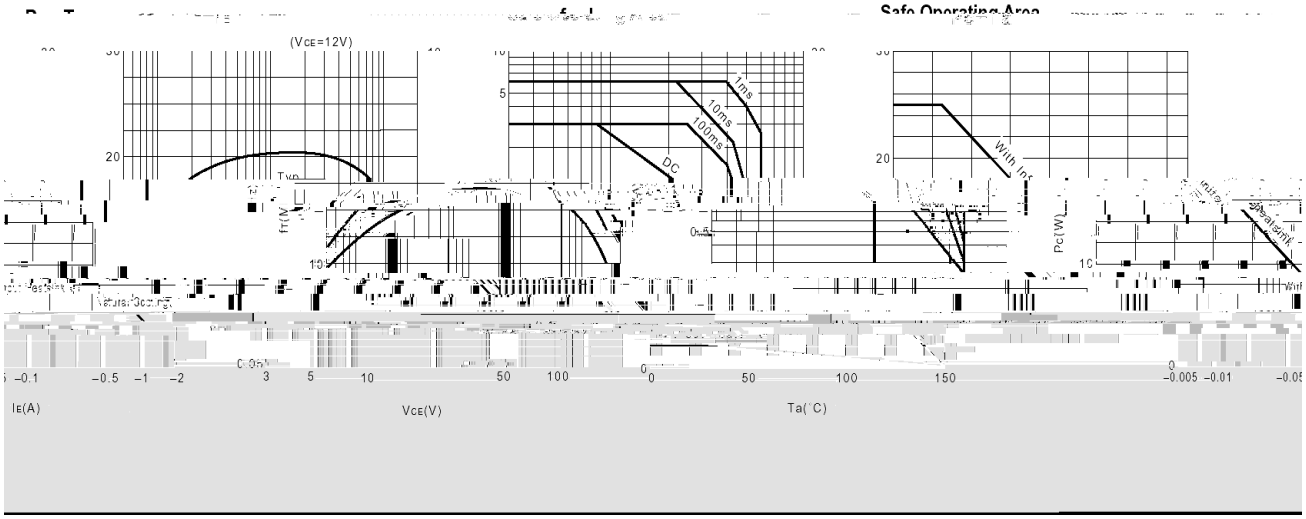
| v ̈Ω<br>Parameter | ϒ N<br>Symbol | Ш ː ̊ Ţ<br>Test Conditions | ώ ṇ Ö<br>Min | Ɛ ʒ Ö<br>Typ | ώ ᶻ Ö<br>Max | D Ч<br>Unit |
|---|---|---|---|---|---|---|
| Collector to Emitter Breakdown Voltage | $V_{CEO}$ | $I_C$=25mA | 60 | | | V |
| Collector Cut-Off Current | $I_{CBO}$ | $V_{CB}$=80V $I_E$=0 | | | 10 | μA |
| Emitter Cut-Off Current | $I_{EBO}$ | $V_{EB}$=6.0V $I_C$=0 | | | 100 | μA |
| DC Current Gain | $h_{FE}$ | $V_{CE}$=4.0V $I_C$=500mA | 500 | | 2000 | |
| Collector to Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C$=2.0A $I_B$=50mA | | | 0.5 | V |
| Transition Frequency | $f_T$ | $V_{CE}$=12V $I_C$=0.2A | | 15 | | MHz |

18.48 ref 18.48 refBT10.5 0 0 10.5 55.98114998 243 0 151]TJ(f)6(cit)9TJce84.268-301C-0.004 Tc0 Tw(T )Tj181 00.4

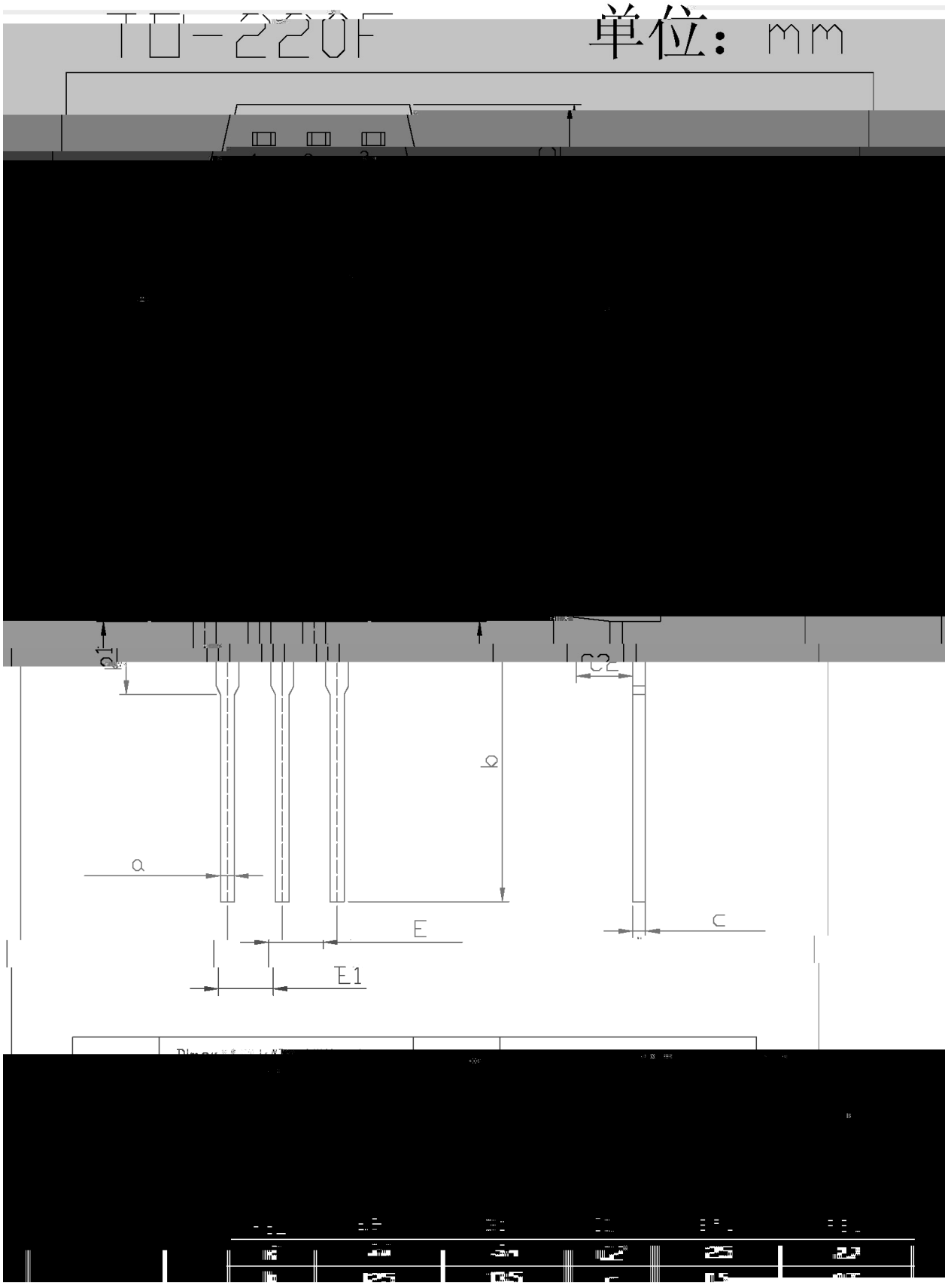
## / Electrical Characteristic Curve



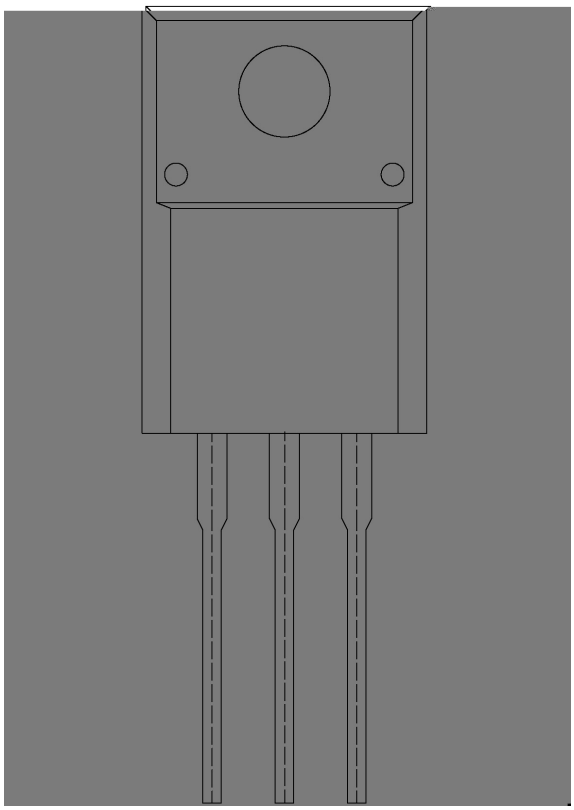



## / Package Dimensions



## / Marking Instructions



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EU χ ѭ ϳ и Ґђ

F6 ; 85 χ ѭ ϲ N Ґђ